Citation Report

List of articles citing

InAs Thin-Channel High-Electron-Mobility Transistors with Very High Current-Gain Cutoff Frequency for Emerging Submillimeter-Wave Applications

DOI: 10.7567/apex.6.034001
Applied Physics Express, 2013, 6, 034001.

#	Paper	IF	Citations
82	Nanometer-scale InGaAs Field-Effect Transistors for THz and CMOS technologies. **2013**,		1
81	Nanometer-scale InGaAs field-effect transistors for THz and CMOS technologies. **2013**,		0
80	Monte Carlo simulation of InAlAs/InGaAs HEMTs with various shape of buried gate. **2014**,		2
79	Comparison between theoretical and experimental results for energy states of two-dimensional electron gas in pseudomorphically strained InAs high-electron-mobility transistors. *Japanese Journal of Applied Physics*, **2014**, 53, 04EF09	1.4	4
78	Cryogenic noise performance of InGaAs/InAlAs HEMTs grown on InP and GaAs substrate. *Solid-State Electronics*, **2014**, 91, 74-77	1.7	15
77	Structural and electrophysical properties of In0.52Al0.48As/In0.53Ga0.47As/In0.52Al0.48As/InP HEMT nanoheterostructures with different combinations of InAs and GaAs inserts in quantum well. *Crystallography Reports*, **2015**, 60, 397-405	0.6	1
76	The Role of the Base Stack on the AC Performance of GaN Hot Electron Transistor. *IEEE Electron Device Letters*, **2015**, 36, 669-671	4.4	2
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